

/ Descriptions

KF (\$) - = E GE Silicon NPN transistor in a TO-126F Plastic Package.

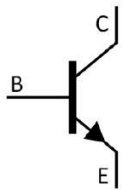
/ Features

Low $V_{CE(sat)}$, high current and high f_T , excellent linearity of h_{FE} , fast switching time.

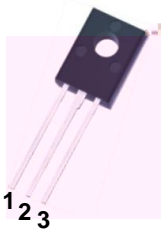
/ Applications

Relay drivers, high-speed inverters, general high-current switching applications.

/ Equivalent Circuit



/ Pinning



PIN1 Emitter PIN 2 Collector PIN 3 Base

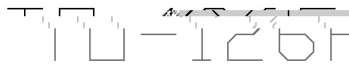
/ h_{FE} Classifications & Marking

h_{FE} Classifications Symbol	M	L	K
h_{FE} Range	100 200	160 320	200 400

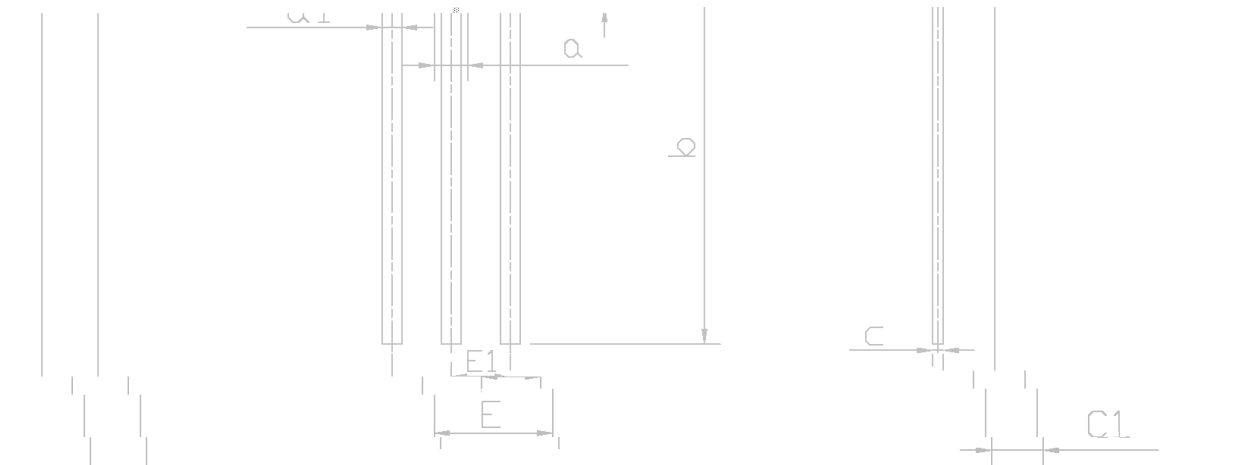
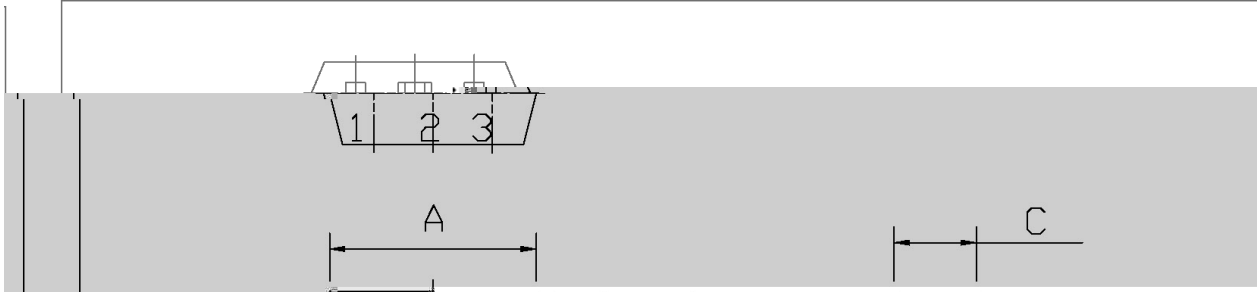
Parameter	Symbol	Rating	Unit
Collector to Base Voltage	V_{CBO}	60	V
Collector to Emitter Voltage	V_{CEO}	60	V
Emitter to Base Voltage	V_{EBO}	7.0	V
Collector Current - Continuous	I_C	3.0	A
Collector Power Dissipation	P_C	2.0	W
Collector Power Dissipation	$P_C(T_c=125^\circ C)$	10	W
Junction Temperature	T_j	150	
Storage Temperature Range	T_{stg}	-55 150	

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit	Á
-----------	--------	-----------------	-----	-----	-----	------	---

/ Package Dimensions

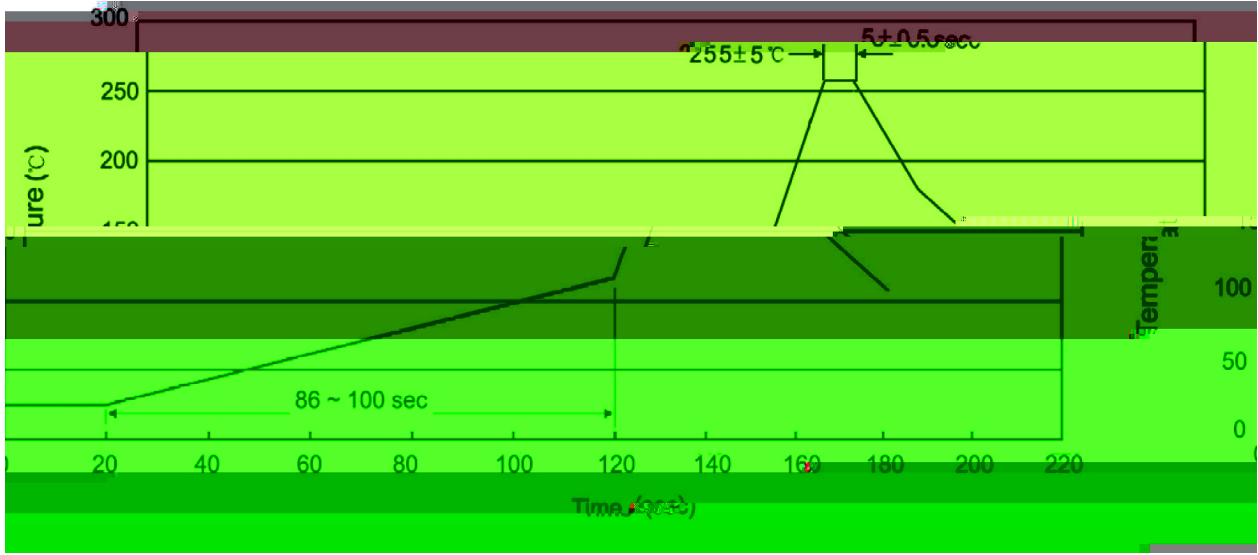


单位: mm



		Dimensions To Millimeters		Dimensions To Millimeters	
Max		Min	Max	Min	
2.96	A	7.8	8.2	2.1	0.66
4.67	B	10.8	11.2	E	4.4
2.9	B1	3.8	4.2	C	3.1
2.1	R	2.95	3.15	C1	1.9
0.6	b	1.4	1.6	c	0.3
	b1		1.9	a	1.2

() / Temperature Profile for Dip Soldering(Pb-Free)



Note:

- | | | | | | |
|---|--------|-----|------------|--------|---|
| 1 | 25 | 150 | 60 | 90sec; | 1.Preheating:25~150 , Time:60~90sec. |
| 2 | 255..5 | | 5..0.5sec; | | 2.Peak Temp.:255..5 , Duration:5..0.5sec. |
| 3 | | 2 | 10 | /sec. | 3. Cooling Speed: 2~10 /sec. |

/ Resistance to Soldering Heat Test Conditions

270..5 10..1 sec. Temp.:270±5 Time:10±1 sec

/ Packaging SPEC.

/ BULK

Package Type 封装形式	Units 包装数量					Dimension 包装尺寸 (unit: mm ³)
	Units/Tube 只/套管	Tubes/Inner Box 套管/盒	Units/Inner Box 只/盒	Inner Boxes/Outer Box 盒/箱	Units/Outer Box 只/箱	